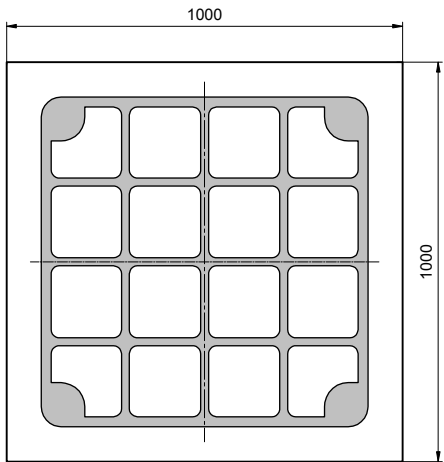


Radiation	Type	Technology	Electrodes
Yellow	solderable	AlInGaP/GaAs	P (anode) up

 PoC-05	typ. dimensions (µm)	
	typ. thickness 260 (±20) µm	
	cathode gold alloy, 1.5 µm	
	anode gold alloy, 1.5 µm	

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		1.8	2.0	V
Forward voltage	I _F = 100 mA	V _F		2.0		V
Reverse voltage	I _F = 10 µA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e	0.45	0.6		mW
Radiant power ¹	I _F = 100 mA	Φ _e		2.8		mW
Luminous intensity ¹	I _F = 100 mA	I _V	400	550		mcd
Peak wavelength	I _F = 100 mA	λ _p	592	595	598	nm
Dominant wavelength	I _F = 100 mA	λ _D		592		nm
Spectral bandwidth at 50%	I _F = 100 mA	Δλ _{0.5}		17		nm
Switching time	I _F = 100 mA	t _r , t _f		25		ns

¹Measured on bare chip on TO-18 header with EPIGAP equipment

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-590-11-05				

Packing: Chips on adhesive film with wire-bond side on top